

< C band internally matched power GaAs FET >

MGFC47B3436

3.4 - 3.6 GHz BAND / 50W

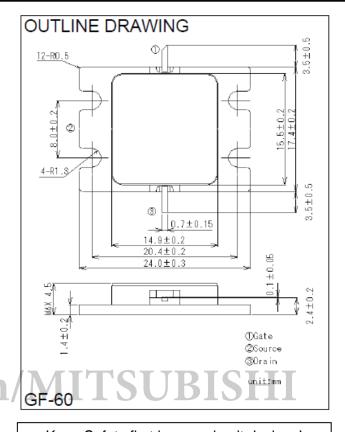
DESCRIPTION

The MGFC47B3436B is an internally impedance-matched GaAs power FET especially designed for use in 3.4-3.6 GHz band amplifiers. The hermetically sealed metal-ceramic package guarantees high reliability.

FEATURES

Class AB operation Internally matched to 50(ohm) system

- High output power Po(SAT)=50W (TYP.) @f=3.4 – 3.6GHz
- High power gain GLP=10.0dB (TYP.) @f=3.4 – 3.6GHz
- Distortion EVM=2.0% (TYP.) @f=3.4 - 3.6GHz, Po=37dBm



RECOMMENDED BIAS CONDITIONS

• VDS=12V • ID=1.5A • RG=10ohm

Absolute maximum ratings (Ta=25°C)

Symbol	Parameter	Ratings	Unit
VGDO	Gate to drain breakdown voltage	-15	V
VGSO	Gate to source breakdown voltage	-10	V
MAXID	Maximum drain current	12	Α
PT *1	Total power dissipation	115	W
Tch	Cannel temperature	175	°C
Tstg	Storage temperature	-55 to +150	°C

*1 : Tc=25°C

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Electrical characteristics (Ta=25°C)

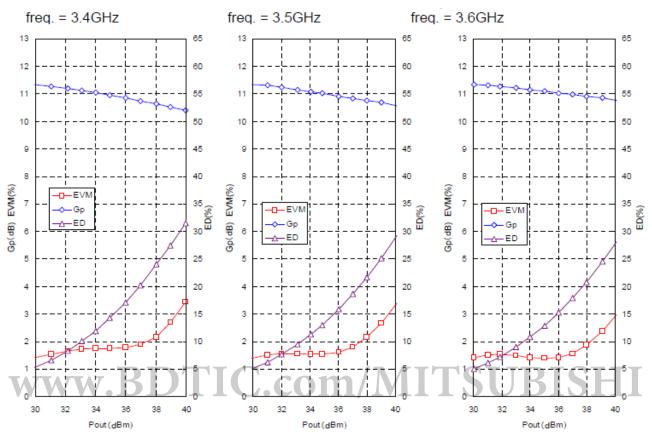
Symbol	Parameter	Test conditions	Limits		Unit	
			Min.	Тур.	Max.	
VGS(off)	Gate to source cut-off voltage	VDS=3V,ID=100mA	-0.5	-	-3.0	V
Po(SAT)	Output Power	VDS=12V,ID(RF off)=1.5A	-	47	-	dBm
		f=3.4 - 3.6GHz				
GP	Power Gain	VDS=12V,ID(RF off)=1.5A	9	10.5	-	dB
ID	Drain current	f=3.4 - 3.6GHz ,Pout=37dBm	-	2.0	3.0	Α
EVM *2	Error Vector Magnitude		-	1.5	2.5	%
Rth(ch-c) *3	Thermal resistance	delta Vf method	-	0.65	1.2	°C/W

^{2:}WiMAX Downlink, 64QAM-3/4, Channel Bandwidth:6MHz

^{*3 :}Channel-case

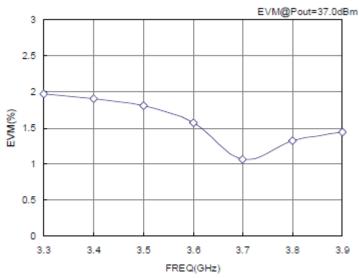
MGFC47B3436B TYPICAL CHARACTERISTICS

EVM,GP,ED(@WiMAX) vs. Pout



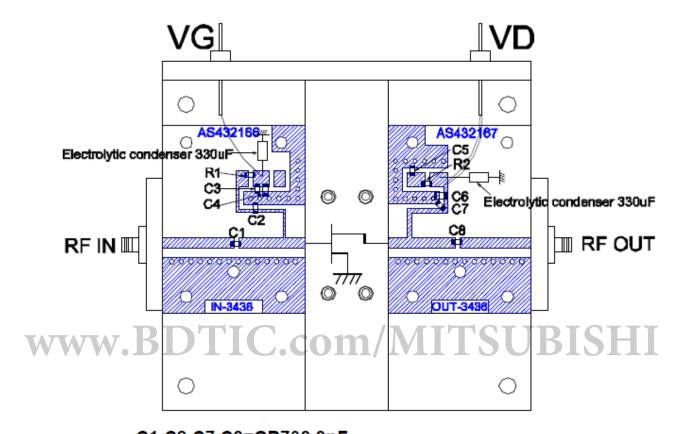
Test Condition Vds=12V,Idq=1.5A,Ta=25deg.C WiMAX:64QAM-3/4,Bw=7MHz

EVM(@WiMAX) vs. f



Test Condition
Vds=12V,ldq=1.5A,Pout=37dBm,Ta=25deg.C
WiMAX:64QAM-3/4,Bw=7MHz

MGFC47B3436B RF TEST FIXTURE



C1,C2,C7,C8=GR708 8pF

C3,C5=1000pF

C4=100nF

C6=470nF

R1= 10ohm

R2=CR10 51ohm

Board material:Teflon t=0.8mm

Specific dielectric constant=2.6

UNIT:(mm)

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